

## ME6970D-VB Datasheet

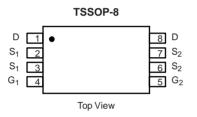
# **Dual N-Channel MOSFET**

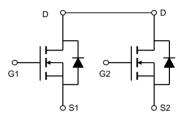
| PRODUCT SUMMARY     |                           |                    |  |  |
|---------------------|---------------------------|--------------------|--|--|
| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω)   | I <sub>D</sub> (A) |  |  |
| 20                  | 0.014 at $V_{GS}$ = 4.5 V | 7.6                |  |  |
| 20                  | 0.018 at $V_{GS}$ = 2.5 V | 6.5                |  |  |

#### FEATURES

- Halogen-free Option Available
- Trench Power MOSFETs







| ABSOLUTE MAXIMUM RATINGS  | T <sub>A</sub> = 25 °C, unles | s otherwise n                     | oted        |              |      |
|---|-------------------------------|-----------------------------------|-------------|--------------|------|
| Parameter   |                               | Symbol                            | 10 s        | Steady State | Unit |
| Drain-Source Voltage  |                               | V <sub>DS</sub>                   | 20          |              | N/   |
| Gate-Source Voltage   |                               | V <sub>GS</sub>                   | ± 12        |              | V    |
| Continuous Drain Quarant (T. 150 %C)a                           | T <sub>A</sub> = 25 °C        | - I <sub>D</sub>                  | 7.6         | 6.2          | •    |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup> | T <sub>A</sub> = 70 °C        |                                   | 6.5         | 4.5          |      |
| Pulsed Drain Current  |                               | I <sub>DM</sub>                   | 30          |              | A    |
| Continuous Source Current (Diode Conduction) <sup>a</sup>       |                               | ۱ <sub>S</sub>                    | 1.5         | 1.0          |      |
|   | T <sub>A</sub> = 25 °C        | P <sub>D</sub>                    | 1.5         | 1.0          | W    |
| Maximum Power Dissipation <sup>a</sup>                          | T <sub>A</sub> = 70 °C        |                                   | 0.96        | 0.64         |      |
| Operating Junction and Storage Temperature Range                |                               | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150 |              | °C   |

| THERMAL RESISTANCE RATINGS               |              |                   |      |      |      |
|--|--------------|-------------------|------|------|------|
| Parameter                                |              | Symbol            | Тур. | Max. | Unit |
|  | t ≤ 10 s     | R <sub>thJA</sub> | 72   | 83   |      |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State |                   | 100  | 120  | °C/W |
| Maximum Junction-to-Foot (Drain)         | Steady State | R <sub>thJF</sub> | 55   | 70   |      |

Notes:

a. Surface Mounted on FR4 board, t  $\leq$  10 s.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

| Parameter                                     | Symbol              | Test Conditions  | Min. | Typ. <sup>a</sup> | Max.  | Unit |  |
|---|---------------------|--|------|-------------------|-------|------|--|
| Static  |                     |  | •    | •                 |       |      |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$ (                             |      |                   | 1.6   | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 V, V_{GS} = \pm 4.5 V$                                   |      |                   | ± 200 | nA   |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | $V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$                |      |                   | 1     |      |  |
|   |                     | $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$ |      |                   | 25 µA |      |  |
| On-State Drain Current <sup>b</sup>           | I <sub>D(on)</sub>  | $V_{DS} \leq 5$ V, $V_{GS}$ = 4.5 V                                  | 30   |                   |       | А    |  |
| Drain-Source On-State Resistance <sup>b</sup> | Б                   | $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$              |      | 0.014             |       |      |  |
|   | R <sub>DS(on)</sub> | $V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 5.5 \text{ A}$              |      | 0.018             |       | Ω    |  |
| Forward Transconductance <sup>b</sup>         | 9 <sub>fs</sub>     | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 6.5 \text{ A}$               |      | 30                |       | S    |  |
| Diode Forward Voltage <sup>b</sup>            | V <sub>SD</sub>     | $I_{S} = 1.5 \text{ A}, V_{GS} = 0 \text{ V}$                        |      | 0.71              | 1.2   | V    |  |
| Dynamic <sup>a</sup>                          |                     |  |      |                   |       |      |  |
| Total Gate Charge                             | Qg                  |  |      | 12                | 18    |      |  |
| Gate-Source Charge                            | Q <sub>gs</sub>     | $V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 6.5 A                   |      | 2.2               |       | nC   |  |
| Gate-Drain Charge                             | Q <sub>gd</sub>     |  |      | 3.6               |       |      |  |
| Turn-On Delay Time                            | t <sub>d(on)</sub>  |  |      | 245               | 365   |      |  |
| Rise Time                                     | t <sub>r</sub>      | $V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$                                 |      | 330               | 495   |      |  |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> | $I_D \cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_G$ = 6 $\Omega$               |      | 860               | 1300  | - ns |  |
| Fall Time                                     | t <sub>f</sub>      |  |      | 510               | 765   |      |  |

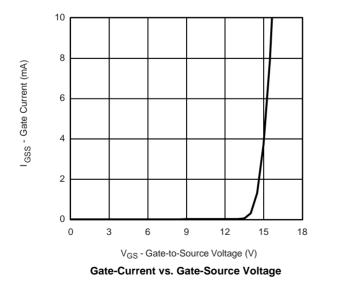
Notes:

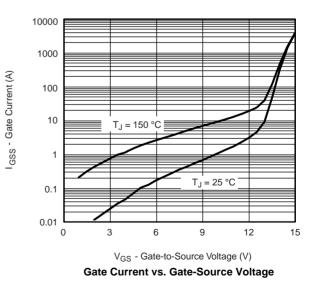
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



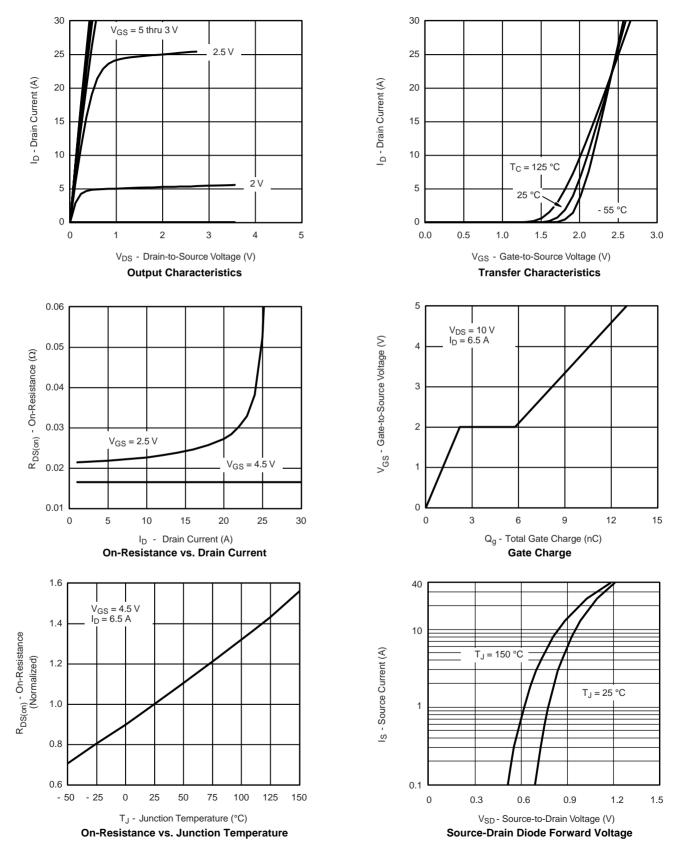


Bsemi

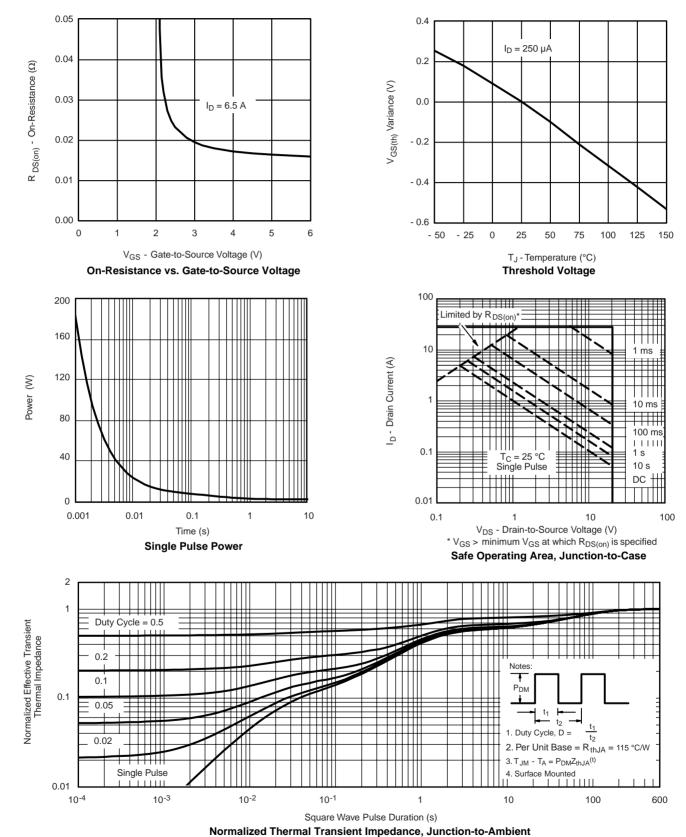
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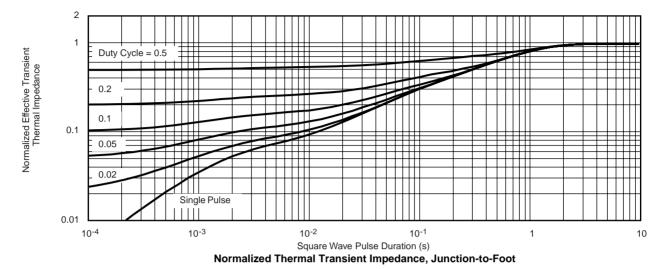


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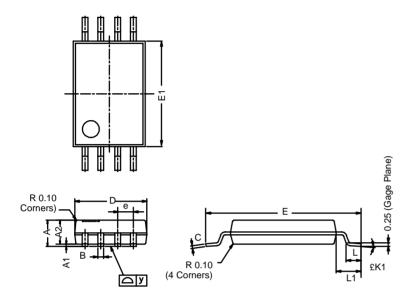


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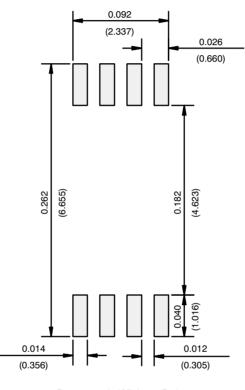
TSSOP: 8-LEAD JEDEC Part Number: MO-153



|   | MILLIMETERS |       |      |  |  |
|---|-------------|-------|------|--|--|
| Dim   | Min         | Max   |      |  |  |
| Α   | -           | -     | 1.20 |  |  |
| <b>A</b> <sub>1</sub>                       | 0.05        | 0.10  | 0.15 |  |  |
| A <sub>2</sub>                              | 0.80        | 1.00  | 1.05 |  |  |
| В   | 0.19        | 0.28  | 0.30 |  |  |
| С   | -           | 0.127 | -    |  |  |
| D   | 2.90        | 3.00  | 3.10 |  |  |
| Е   | 6.20        | 6.40  | 6.60 |  |  |
| E <sub>1</sub>                              | 4.30        | 4.40  | 4.50 |  |  |
| е   | -           | 0.65  | -    |  |  |
| L   | 0.45        | 0.60  | 0.75 |  |  |
| L <sub>1</sub>                              | 0.90        | 1.00  | 1.10 |  |  |
| Y   | -           | -     | 0.10 |  |  |
| £ <b>K1</b>                                 | 0°          | 3°    | 6°   |  |  |
| ECN: S-03946—Rev. G, 09-Jul-01<br>DWG: 5844 |             |       |      |  |  |



#### **RECOMMENDED MINIMUM PADS FOR TSSOP-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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